PMV185XN

30 V, single N-channel Trench MOSFET

3 August 2012

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low R_{DSon}
- Very fast switching
- Trench MOSFET technology

1.3 Applications

- · Relay driver
- · High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|------------------------|----------------------------------|--|-----|-----|-----|-----|------|
| V _{DS} | drain-source voltage | T _{amb} = 25 °C | | - | - | 30 | V |
| V_{GS} | gate-source voltage | | | -12 | - | 12 | V |
| I _D | drain current | V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s | [1] | - | - | 1.2 | Α |
| Static characteristics | | | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 4.5 \text{ V}; I_D = 1.1 \text{ A}; T_j = 25 ^{\circ}\text{C}$ | | - | 185 | 250 | mΩ |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





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2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|--|
| 1 | G | gate | <u> </u> | D |
| 2 | S | source | | |
| 3 | D | drain | 1 | G 13 7 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 |
| | | | | 017aaa253 |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | |
|-------------|----------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| PMV185XN | TO-236AB | plastic surface-mounted package; 3 leads | SOT23 | | | |

4. Marking

Table 4. Marking codes

| 144010 11 11411111111111111111111111111 | | | | | |
|---|--------------|--|--|--|--|
| Type number | Marking code | | | | |
| | [1] | | | | |
| PMV185XN | EH% | | | | |

^{[1] % =} placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|--|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _{amb} = 25 °C | | - | 30 | V |
| V _{GS} | gate-source voltage | | | -12 | 12 | V |
| I _D | drain current | V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s | [1] | - | 1.2 | Α |
| | | V _{GS} = 4.5 V; T _{amb} = 25 °C | [1] | - | 1.1 | Α |
| | | V _{GS} = 4.5 V; T _{amb} = 100 °C | [1] | - | 0.7 | Α |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$ | | - | 4.4 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 325 | mW |
| | | | [1] | - | 455 | mW |
| | | T _{sp} = 25 °C | | - | 1275 | mW |

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| Symbol | Parameter | Conditions | | Min | Max | Unit |
|--------------------|----------------------|--------------------------|-----|-----|-----|------|
| Tj | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-drain diode | | | | | | |
| I _S | source current | T _{amb} = 25 °C | [1] | - | 0.7 | Α |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

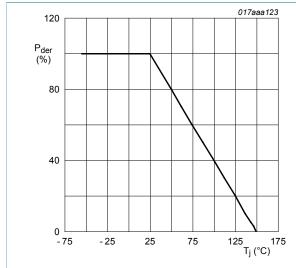


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

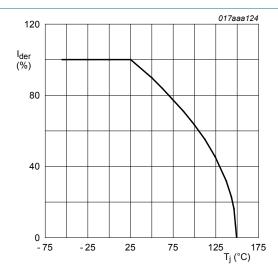


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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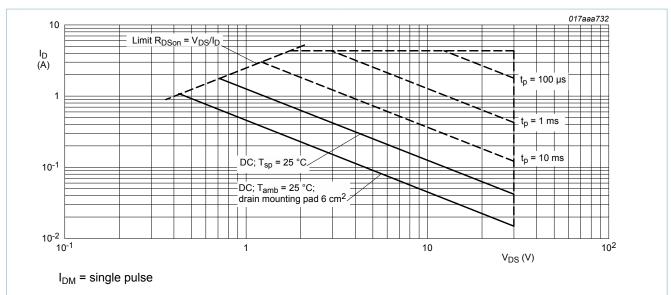


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--|--|----------------------|-----|-----|-----|-----|------|
| R _{th(j-a)} thermal resistance from junction to ambient | | | [1] | - | 333 | 385 | K/W |
| | | | [2] | - | 240 | 275 | K/W |
| | ambient | in free air; t ≤ 5 s | [2] | - | 203 | 235 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 85 | 100 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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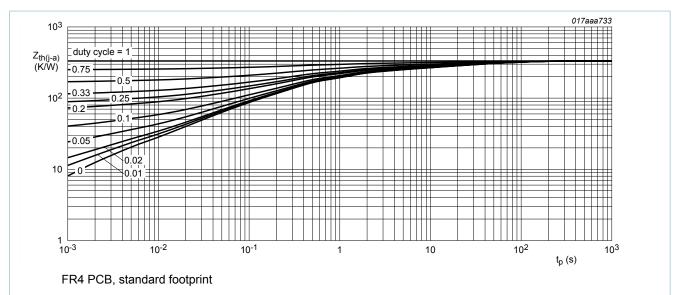


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

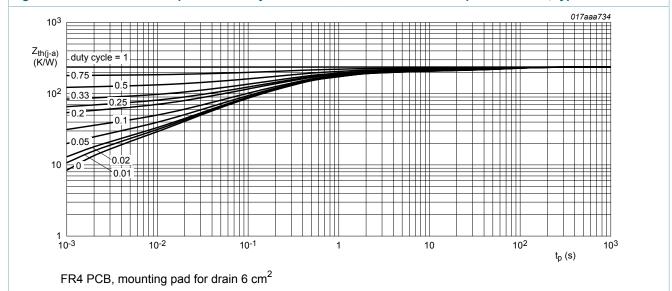


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------|-----------------------------------|--|-----|-----|---------------|-----------------|
| Static chara | acteristics | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | I_D = 250 μ A; V_{GS} = 0 V; T_j = 25 °C | 30 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$ | 0.5 | 1 | 1.5 | V |
| I _{DSS} | drain leakage current | V _{DS} = 30 V; V _{GS} = 0 V; T _{amb} = 25 °C | - | - | 1 | μA |
| | | V _{DS} = 30 V; V _{GS} = 0 V; T _{amb} = 150 °C | - | - | 10 | μA |
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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|------------------------------|---|----------|------|-----|------|
| I _{GSS} | gate leakage current | V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 100 | nA |
| | | V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 100 | nA |
| R _{DSon} | drain-source on-state | V _{GS} = 4.5 V; I _D = 1.1 A; T _j = 25 °C | - | 185 | 250 | mΩ |
| | resistance | V _{GS} = 4.5 V; I _D = 1.1 A; T _j = 150 °C | - | 300 | 400 | mΩ |
| | | $V_{GS} = 2.5 \text{ V}; I_D = 0.25 \text{ A}; T_j = 25 ^{\circ}\text{C}$ | - | 255 | 365 | mΩ |
| 9 _{fs} | forward transconductance | V_{DS} = 10 V; I_{D} = 1.1 A; T_{j} = 25 °C | - | 2.9 | - | S |
| Dynamic cl | haracteristics | | <u> </u> | | | |
| Q _{G(tot)} | total gate charge | V _{DS} = 15 V; I _D = 1.1 A; V _{GS} = 4.5 V; | - | 0.87 | 1.3 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 0.17 | - | nC |
| Q_{GD} | gate-drain charge | | - | 0.24 | - | nC |
| C _{iss} | input capacitance | V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V; | - | 76 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 30 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 22 | - | pF |
| t _{d(on)} | turn-on delay time | V _{DS} = 15 V; I _D = 1.1 A; V _{GS} = 4.5 V; | - | 7 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$ | - | 11 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 16 | - | ns |
| t _f | fall time | | - | 7 | - | ns |
| Source-dra | in diode | | l I | | | |
| V _{SD} | source-drain voltage | $I_S = 0.7 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | 0.8 | 1.2 | V |

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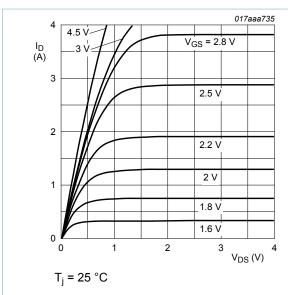
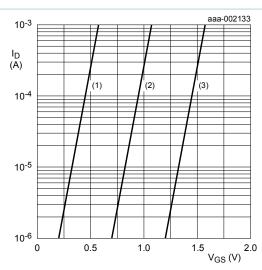


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \,^{\circ}C; V_{DS} = 5 \,^{\circ}V$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

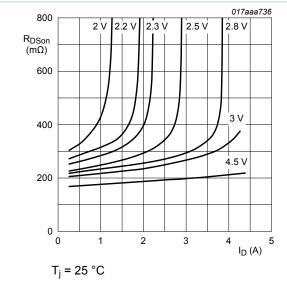


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

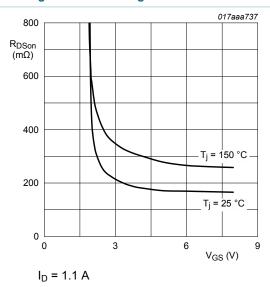


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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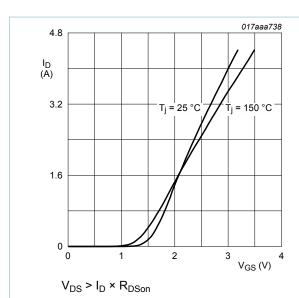


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

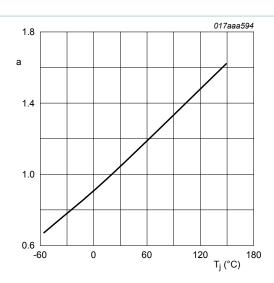


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

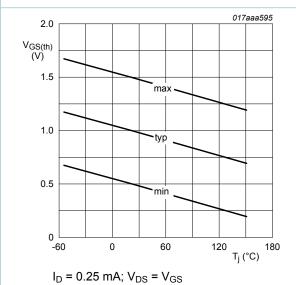


Fig. 12. Gate-source threshold voltage as a function of junction temperature

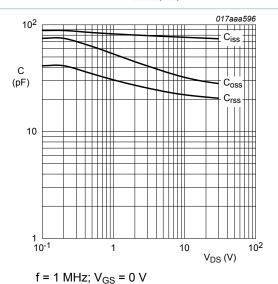


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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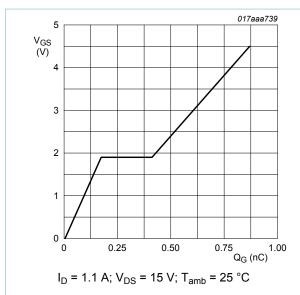


Fig. 14. Gate-source voltage as a function of gate charge; typical values

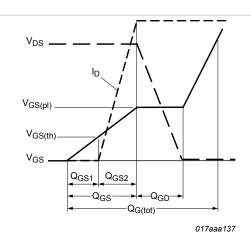


Fig. 15. Gate charge waveform definitions

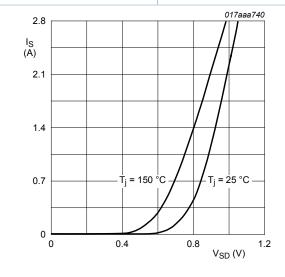
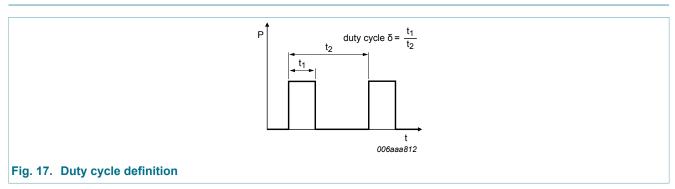


Fig. 16. Source current as a function of source-drain voltage; typical values

8. Test information

 $V_{GS} = 0 V$



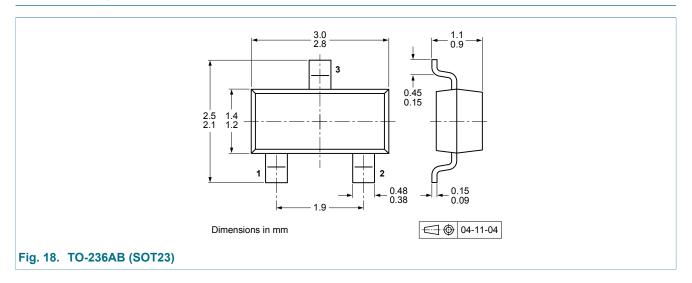
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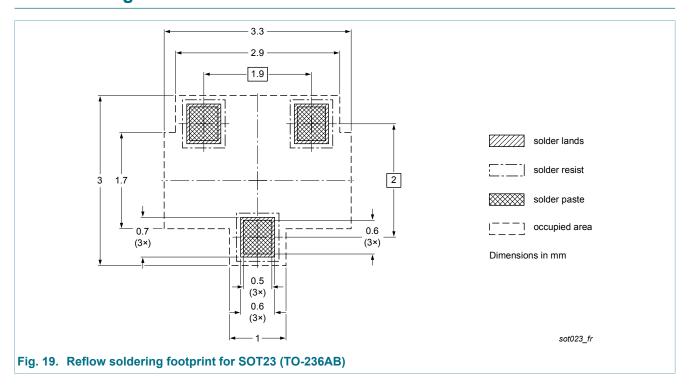
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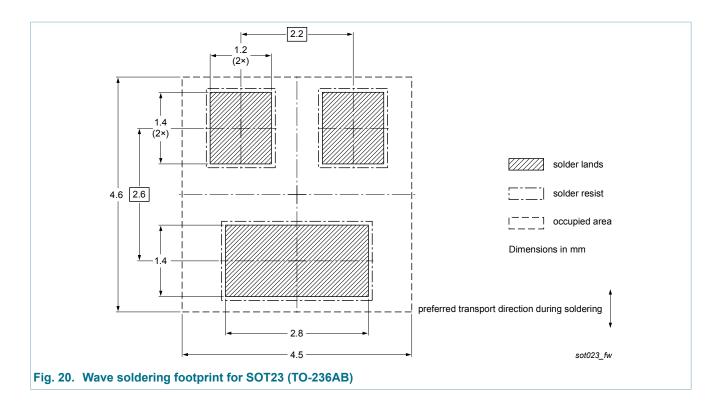
9. Package outline



10. Soldering



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11. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PMV185XN v.1 | 20120803 | Product data sheet | - | - |

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12. Legal information

12.1 Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
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